

Maksim G Kozodaev

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8291063/publications.pdf>

Version: 2024-02-01

31
papers

1,197
citations

586496

16
h-index

466096

32
g-index

32
all docs

32
docs citations

32
times ranked

1204
citing authors

#	ARTICLE	IF	CITATIONS
1	Microextrusion printing of gas-sensitive planar anisotropic NiO nanostructures and their surface modification in an H ₂ S atmosphere. Applied Surface Science, 2022, 578, 151984.	3.1	23
2	Origin of the retention loss in ferroelectric Hf _{0.5} Zr _{0.5} O ₂ -based memory devices. Acta Materialia, 2021, 204, 116515.	3.8	36
3	Band Alignment of Graphene/MoS ₂ /Fluorine Tin Oxide Heterojunction for Photodetector Application. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000744.	0.8	1
4	Electroresistance effect in MoS ₂ -Hf _{0.5} Zr _{0.5} O ₂ heterojunctions. Applied Physics Letters, 2021, 118, .	1.5	13
5	Microplotter printing of planar solid electrolytes in the CeO ₂ -Y ₂ O ₃ system. Journal of Colloid and Interface Science, 2021, 588, 209-220.	5.0	28
6	Interface engineering for enhancement of the analog properties of W/WO ₃ /HfO ₂ /Pd resistance switched structures. Journal Physics D: Applied Physics, 2021, 54, 504004.	1.3	8
7	Thickness-Dependent Structural and Electrical Properties of WS ₂ Nanosheets Obtained via the ALD-Grown WO ₃ Sulfurization Technique as a Channel Material for Field-Effect Transistors. ACS Omega, 2021, 6, 34429-34437.	1.6	16
8	Forming-Free Nonfilamentary Resistive Switching in W/WO ₃ /HfO ₂ /Pd Structures. Nanobiotechnology Reports, 2021, 16, 737-744.	0.2	3
9	Band Alignment in As-Transferred and Annealed Graphene/MoS ₂ Heterostructures. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900406.	1.2	14
10	Influence of ALD Ru bottom electrode on ferroelectric properties of Hf _{0.5} Zr _{0.5} O ₂ -based capacitors. Applied Physics Letters, 2020, 117, .	1.5	15
11	Radical-Enhanced Atomic Layer Deposition of a Tungsten Oxide Film with the Tunable Oxygen Vacancy Concentration. Journal of Physical Chemistry C, 2020, 124, 18156-18164.	1.5	14
12	Influence of Reducing Agent on Properties of Thin WS ₂ Nanosheets Prepared by Sulfurization of Atomic Layer-Deposited WO ₃ . Journal of Physical Chemistry C, 2020, 124, 28169-28177.	1.5	9
13	Resistance Switching Peculiarities in Nonfilamentary Self-Rectified TiN/Ta ₂ O ₅ /Ta and TiN/HfO ₂ /Ta ₂ O ₅ /Ta Stacks. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900952.	0.8	18
14	Pen plotter printing of Co ₃ O ₄ thin films: features of the microstructure, optical, electrophysical and gas-sensing properties. Journal of Alloys and Compounds, 2020, 832, 154957.	2.8	38
15	Ferroelectric Second-Order Memristor. ACS Applied Materials & Interfaces, 2019, 11, 32108-32114.	4.0	77
16	Synthesis of Large Area Two-Dimensional MoS ₂ Films by Sulfurization of Atomic Layer Deposited MoO ₃ Thin Film for Nanoelectronic Applications. ACS Applied Nano Materials, 2019, 2, 7521-7531.	2.4	34
17	Temperature controlled Ru and RuO ₂ growth via O* radical-enhanced atomic layer deposition with Ru(EtCp) ₂ . Journal of Chemical Physics, 2019, 151, 204701.	1.2	18
18	Mitigating wakeup effect and improving endurance of ferroelectric HfO ₂ -ZrO ₂ thin films by careful La-doping. Journal of Applied Physics, 2019, 125, .	1.1	110

#	ARTICLE	IF	CITATIONS
19	Size-ordered 63Ni nanocluster film as a betavoltaic battery unit. Applied Physics Letters, 2018, 112, .	1.5	5
20	Improved Ferroelectric Switching Endurance of La-Doped Hf _{0.5} Zr _{0.5} O ₂ Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 2701-2708.	4.0	207
21	La-doped Hf _{0.5} Zr _{0.5} O ₂ thin films for high-efficiency electrostatic supercapacitors. Applied Physics Letters, 2018, 113, .	1.5	43
22	Leakage Currents Mechanism in Thin Films of Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ . ECS Transactions, 2017, 75, 123-129.	0.3	13
23	Low temperature plasma-enhanced ALD TiN ultrathin films for Hf _{0.5} Zr _{0.5} O ₂ -based ferroelectric MIM structures. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700056.	0.8	20
24	Ferroelectric properties of lightly doped La:HfO ₂ thin films grown by plasma-assisted atomic layer deposition. Applied Physics Letters, 2017, 111, .	1.5	69
25	Leakage currents mechanism in thin films of ferroelectric Hf _{0.5} Zr _{0.5} O ₂ . Journal of Physics: Conference Series, 2017, 864, 012002.	0.3	4
26	Ferroelectric properties of full plasma-enhanced ALD TiN/La:HfO ₂ /TiN stacks. Applied Physics Letters, 2016, 108, .	1.5	79
27	Charge transport in thin layers of ferroelectric Hf _{0.5} Zr _{0.5} O ₂ . Russian Microelectronics, 2016, 45, 350-356.	0.1	1
28	Ultrathin Hf _{0.5} Zr _{0.5} O ₂ Ferroelectric Films on Si. ACS Applied Materials & Interfaces, 2016, 8, 7232-7237.	4.0	186
29	Charge transport mechanism in thin films of amorphous and ferroelectric Hf _{0.5} Zr _{0.5} O ₂ . JETP Letters, 2015, 102, 544-547.	0.4	25
30	Structural, chemical and electrical properties of ALD-grown Hf _x Al _{1-x} O _y thin films for MIM capacitors. Physica Status Solidi (B): Basic Research, 2015, 252, 701-708.	0.7	4
31	Confinement-free annealing induced ferroelectricity in Hf _{0.5} Zr _{0.5} O ₂ thin films. Microelectronic Engineering, 2015, 147, 15-18.	1.1	64